

**AMENDMENTS TO THE CLAIMS:**

*This listing of claims will replace all prior versions, and listings, of claims in the application:*

1-11. (Canceled)

12. (Currently amended) A production apparatus of a film, comprising:

means for heating a substrate comprising silicon,

plural dispersion heads for discharging independently gaseous compounds for forming the film,

means for positioning a bottom discharge end of a former dispersion head closer to a surface of the substrate than is a bottom discharge end of a latter dispersion head,

means for conveying the silicon substrate heated to a predetermined temperature in a direction from a position immediately below a discharge port of the former dispersion head to a position immediately below discharge ports of the latter dispersion heads, and

a partition provided between the dispersion heads and the silicon substrate, the partition being positioned at a circumference of bottom ends of dispersion ports of the latter dispersion head.

13. (Canceled)

14. (Currently amended) The apparatus of claim 12, wherein said means for positioning and means for conveying cause [[the]] a titanium oxide film to be formed in a non-uniform manner so that a concentration of the dopant element in the film varies through a thickness of the

film so that the concentration of the dopant element in the titanium oxide film is higher adjacent a surface of the substrate than at a location spaced further away from the surface of the substrate.

15. (New) The apparatus of claim 12, wherein a difference between (i) a distance "A" from the bottom discharge end of the former dispersion head, and (ii) a distance "B" from the bottom discharge end of the latter dispersion head to the surface of the silicon substrate is from 0.1 to 30 mm.